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NTE2693 (NPN) & NTE2694 (PNP) Silicon Complementary Transistors Darlington, General Purpose, Audio TO-220 Full Pack

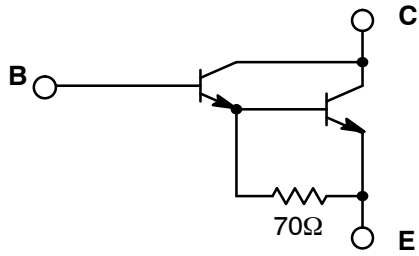
Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	110V
Collector-Emitter Voltage, V_{CEO}	110V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	6A
Base Current, I_B	1A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	30W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 110V$	-	-	100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V$	-	-	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 30\text{mA}$	110	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = 4V, I_C = 5A$	5000	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 5\text{mA}$	-	-	2.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 5A, I_E = 5\text{mA}$	-	-	3.0	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 12V, I_E = -0.5A$	-	60	-	MHz
Capacitance	C_{OB}	$V_{CB} = 10V, f = 1\text{MHz}$	-	55	-	pF

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